

Silicon NPN transistor epitaxial type

C5919

[Applications]

DC/DC relay drivers, lamp drivers, motor drivers, strobes

[Feature]

Very low collector-emitter saturation voltage VCE(sat)= 0.3V (Max.) at IC= 3A, IB= 60mA

[Absolute maximum ratings (Ta=25C)]

Characteristic	Symbol	Maximum ratings	Unit
Collector-base voltage	VCBO	15	V
Collector-emitter voltage	VCEO	15	V
Emitter-base voltage	VEBO	5	V
Collector current (DC)	IC	6	A
Collector current (Pulse)	ICP	9	A
Junction temperature	Tj	150	C
Storage temperature	Tstg	-55 to 150	C

[Electrical characteristics (Ta=25C)]

Characteristic	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BVCBO	15	-	-	V	IC= 10uA
Collector-emitter breakdown voltage	BVCEO	15	-	-	V	IC= 1mA
Emitter-base breakdown voltage	BVEBO	5	-	-	V	IE= 10uA
Collector cut-off current	ICBO	-	-	100	nA	VCB= 12V
Emitter cut-off current	IEBO	-	-	100	nA	VEB= 4V
DC current gain	hFE	250	-	-	-	VCE= 2V, IC= 0.5A
Collector-emitter saturation voltage 1	VCE(sat) 1	-	-	0.18	V	IC= 1.5A, IB= 30mA
Collector-emitter saturation voltage 2	VCE(sat) 2	-	-	0.3	V	IC= 3A, IB= 60mA
Base-emitter saturation voltage	VBE(sat)	-	-	1.2	V	IC= 1.5A, IB= 30mA
Transition frequency	fT	-	250	-	MHz	VCE= 2V, IE= -0.5A
Collector output capacitance	Cob	-	33	-	pF	VCB= 10V, f = 1MHz, IE= 0A
Turn on time	ton	-	35	-	ns	VCC= 5V, IC= 1.5A IB1= -IB2= 75mA
Storage time	tstg	-	135	-	ns	
Fall time	sf	-	5	-	ns	

Notice 1) These are measured data of transistors assembled by PHENITEC SEMICONDUCTOR Corp. and are for reference only.

Notice 2) The contents described herein are subject to change without notice.

